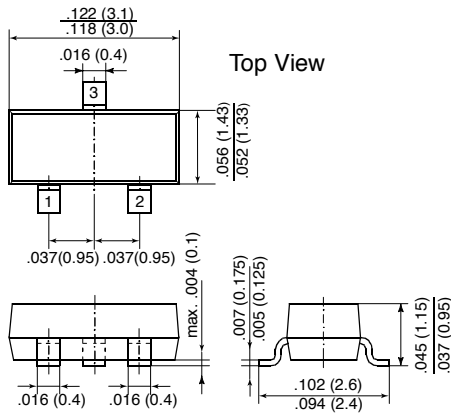


MMBT3906

SMALL SIGNAL TRANSISTORS (PNP)

SOT-23



Dimensions in inches and (millimeters)

Pin configuration

1 = Base, 2 = Emitter, 3 = Collector.

FEATURES

- ◆ PNP Silicon Epitaxial Planar Transistor for switching and amplifier applications.
- ◆ As complementary type, the NPN transistor MMBT3904 is recommended.
- ◆ This transistor is also available in the TO-92 case with the type designation 2N3906.



MECHANICAL DATA

Case: SOT-23 Plastic Package

Weight: approx. 0.008g

Marking code: 2A

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$-V_{CBO}$	40	V
Collector-Emitter Voltage	$-V_{CEO}$	40	V
Emitter-Base Voltage	$-V_{EBO}$	5.0	V
Collector Current	$-I_C$	200	mA
Power Dissipation at $T_A = 25^\circ\text{C}$	P_{tot}	225 ⁽¹⁾ 300 ⁽²⁾	mW mW
Thermal Resistance Junction to Substrate Backside	$R_{\theta SB}$	320 ⁽¹⁾	°C/W
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	450 ⁽¹⁾	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-55 to +150	°C

NOTES:

(1) Device on fiberglass substrate, see layout

(2) Device on alumina substrate

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ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	MIN.	MAX.	UNIT
Collector-Base Breakdown Voltage at $-I_C = 10 \mu\text{A}$, $I_E = 0$	$-V_{(BR)CBO}$	40	–	V
Collector-Emitter Breakdown Voltage at $-I_C = 1 \text{ mA}$, $I_B = 0$	$-V_{(BR)CEO}$	40	–	V
Emitter-Base Breakdown Voltage at $-I_E = 10 \mu\text{A}$, $I_C = 0$	$-V_{(BR)EBO}$	5	–	V
Collector Saturation Voltage at $-I_C = 10 \text{ mA}$, $-I_B = 1 \text{ mA}$ at $-I_C = 50 \text{ mA}$, $-I_B = 5 \text{ mA}$	$-V_{CEsat}$ $-V_{CEsat}$	– –	0.25 0.4	V V
Base Saturation Voltage at $-I_C = 10 \text{ mA}$, $-I_B = 1 \text{ mA}$ at $-I_C = 50 \text{ mA}$, $-I_B = 5 \text{ mA}$	$-V_{BEsat}$ $-V_{BEsat}$	– –	0.85 0.95	V V
Collector-Emitter Cutoff Current at $-V_{EB} = 3 \text{ V}$, $-V_{CE} = 30 \text{ V}$	$-I_{CEV}$	–	50	nA
Emitter-Base Cutoff Current at $-V_{EB} = 3 \text{ V}$, $-V_{CE} = 30 \text{ V}$	$-I_{EBV}$	–	50	nA
DC Current Gain at $-V_{CE} = 1 \text{ V}$, $-I_C = 0.1 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_C = 1 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_C = 10 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_C = 50 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_C = 100 \text{ mA}$	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	60 80 100 60 30	– – 300 – –	– – – – –
Input Impedance at $-V_{CE} = 10 \text{ V}$, $-I_C = 1 \text{ mA}$, $f = 1 \text{ kHz}$	h_{ie}	1	10	k Ω
Gain-Bandwidth Product at $-V_{CE} = 20 \text{ V}$, $-I_C = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	250	–	MHz
Collector-Base Capacitance at $-V_{CB} = 5 \text{ V}$, $f = 100 \text{ kHz}$	C_{CBO}	–	4.5	pF
Emitter-Base Capacitance at $-V_{EB} = 0.5 \text{ V}$, $f = 100 \text{ kHz}$	C_{EBO}	–	10	pF

MMBT3906

ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	MIN.	MAX.	UNIT
Voltage Feedback Ratio at $-V_{CE} = 10 \text{ V}$, $-I_C = 1 \text{ mA}$, $f = 1 \text{ kHz}$	h_{re}	$0.5 \cdot 10^{-4}$	$8 \cdot 10^{-4}$	–
Small Signal Current Gain at $-V_{CE} = 10 \text{ V}$, $-I_C = 1 \text{ mA}$, $f = 1 \text{ kHz}$	h_{fe}	100	400	–
Output Admittance at $-V_{CE} = 1 \text{ V}$, $-I_C = 1 \text{ mA}$, $f = 1 \text{ kHz}$	h_{oe}	1	40	μS
Noise Figure at $-V_{CE} = 5 \text{ V}$, $-I_C = 100 \mu\text{A}$, $R_G = 1 \text{ k}\Omega$, $f = 10 \dots 15 \text{ 000 Hz}$	NF	–	4	dB
Delay Time (see Fig. 1) at $-I_{B1} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	t_d	–	35	ns
Rise Time (see Fig. 1) at $-I_{B1} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	t_r	–	35	ns
Storage Time (see Fig. 2) at $I_{B1} = -I_{B2} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	t_s	–	225	ns
Fall Time (see Fig. 2) at $I_{B1} = -I_{B2} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	t_f	–	75	ns

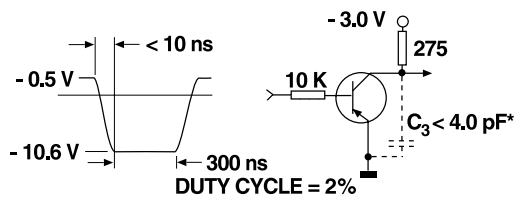


Fig. 1: Test circuit for delay and rise time
* total shunt capacitance of test jig and connectors

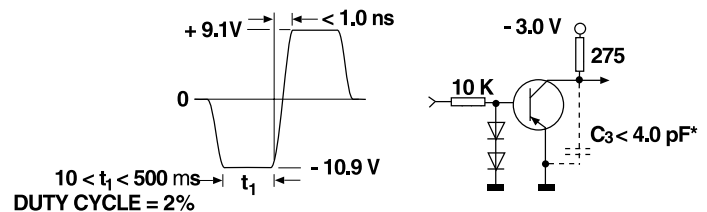
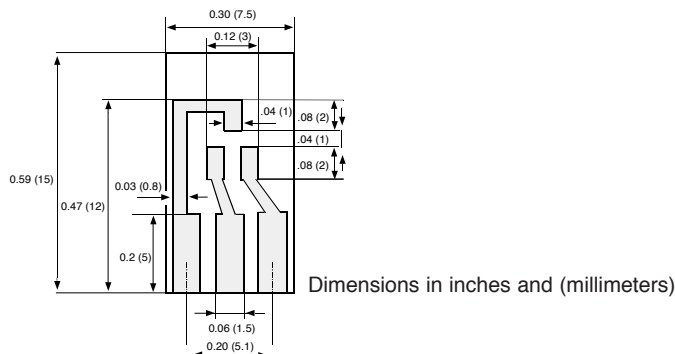


Fig. 2: Test circuit for storage and fall time
* total shunt capacitance of test jig and connectors



Layout for R_{thJA} test

Thickness: Fiberglass 0.059 in (1.5 mm)
Copper leads 0.012 in (0.3 mm)